Product data sheet

1. General description

Ultrafast diode in a TO3PF package.

2. Features and benefits

- Isolated plastic package
- Low leakage current
- · Low reverse recovery current
- · Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- · Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- · Half-bridge / full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

| Table 1. Quick | reference data | | | | | |
|--------------------|-------------------------------------|---|-----|------|-----|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| V_R | reverse voltage | DC | - | - | 600 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; T _h \leq 73 °C; square-wave; Fig. 1; Fig. 2; Fig. 3 | - | - | 30 | Α |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 µs; square-wave | - | - | 60 | Α |
| I _{FSM} | non-repetitive peak forward current | t _p = 10 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 4</u> | - | - | 170 | Α |
| | | t _p = 8.3 ms; T _{j(init)} = 25 °C; SIN | - | - | 190 | Α |
| Static charac | teristics | | | | | |
| V _F | forward voltage | I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u> | - | 1.35 | 1.8 | V |
| | | I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u> | - | 0.96 | - | V |
| Dynamic cha | racteristics | | | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7 | - | 37 | 65 | ns |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_j = 25 ^{\circ}C; Fig. 7$ | - | 85 | - | ns |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ $\mu s; T_i = 125 \text{ °C}; Fig. 7$ | - | 138 | - | ns |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--------------------|----------------|
| 1 | А | anode | mb O _ O | K — A |
| 2 | K | cathode | | 001aaa020 |
| 3 | Α | anode | 0 0 | |
| mb | n.c. | mounting base; isolated | TO3PF | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|--------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| BYV30JT-600P | TO3PF | Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack' | TO3PF | | |

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|---------------------------------|---|-----|-----|------|
| V_{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V_{RWM} | crest working reverse voltage | | - | 600 | V |
| V_R | reverse voltage | DC | - | 600 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; T _h \leq 73 °C; square-wave; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u> | - | 30 | Α |
| I _{O(AV)} | average output current | $\delta = 0.5$; $T_h \le 73$ °C; SQW | - | 60 | Α |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 µs; square-wave | - | 60 | А |
| I _{FSM} | non-repetitive peak | t _p = 10 ms; T _{j(init)} = 25 °C; SIN; <u>Fig. 4</u> | - | 170 | Α |
| | forward current | t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN | - | 190 | Α |
| T _{stg} | storage temperature | | -65 | 175 | °C |
| Tj | junction temperature | | - | 175 | °C |

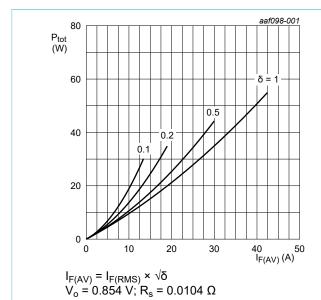


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; typical values

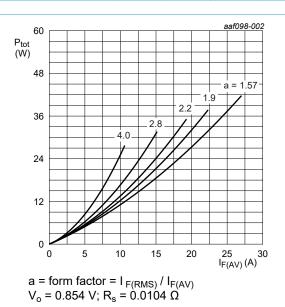
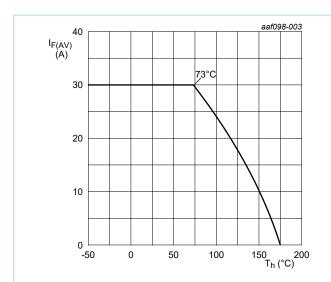


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; typical values





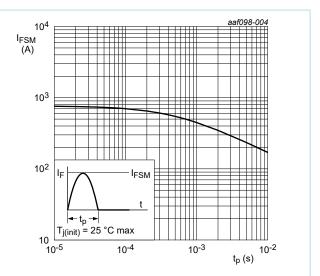


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--------------------------------|-----|-----|-----|------|
| R _{th(j-h)} | thermal resistance from junction to heatsink | With heatsink compound; Fig. 5 | - | 2.3 | 2.6 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | in free air | - | 35 | - | K/W |

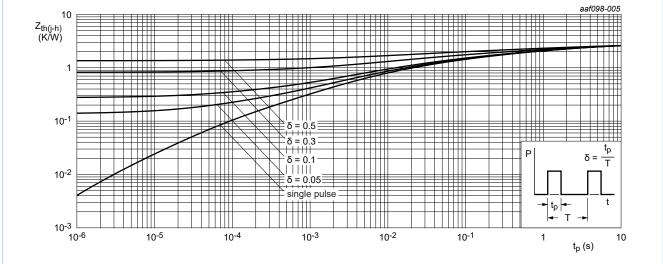
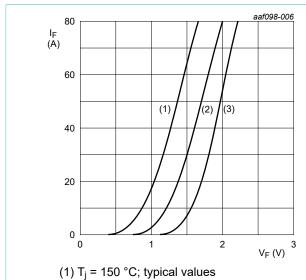


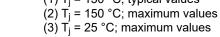
Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values

9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|-------------------------------|---|-----|------|-----|------|
| Static chara | acteristics | | ' | | | |
| V _F | forward voltage | I _F = 30 A; T _j = 25 °C; <u>Fig. 6</u> | - | 1.35 | 1.8 | V |
| | | I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u> | - | 0.96 | - | V |
| I _R | reverse current | V _R = 600 V; T _j = 25 °C | - | - | 10 | μA |
| | | V _R = 600 V; T _j = 150 °C | - | - | 500 | μA |
| Dynamic ch | naracteristics | | · | | | |
| t _{rr} | reverse recovery time | $I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$ | - | 37 | 65 | ns |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 85 | - | ns |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$ | - | 138 | - | ns |
| I _{RM} | peak reverse recovery current | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 \text{ °C}$ | - | 11 | - | Α |
| | | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}$ | - | 18 | - | Α |
| Q _r | recovered charge | $I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 25 ^{\circ}\text{C}; Fig. 7$ | - | 461 | - | nC |
| | | I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _i = 125 °C; <u>Fig. 7</u> | - | 1227 | - | nC |







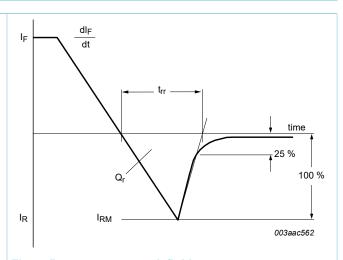
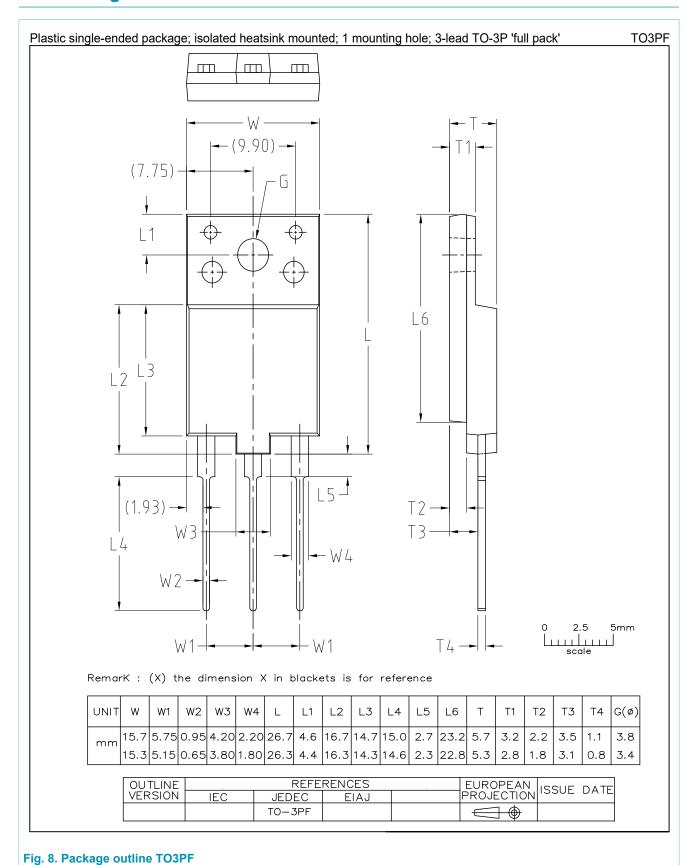


Fig. 7. Reverse recovery definitions; ramp recovery

10. Package outline

BYV30JT-600P



11. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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Ultrafast recovery diode

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